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**(71) Applicant(s):**

HUAWEI TECHNOLOGIES CO., LTD. [CN/CN]; Huawei Administration Building Bantian, Longgang District Shenzhen, Guangdong 518129 (CN) *(for all designated states)*

**(72) Inventor(s):**

LYU, Quan; Huawei Administration Building Bantian, Longgang District Shenzhen, Guangdong 518129 (CN)

XU, Gang; Huawei Administration Building Bantian, Longgang District Shenzhen, Guangdong 518129 (CN)

LIU, Shuyi; Huawei Administration Building Bantian, Longgang District Shenzhen, Guangdong 518129 (CN)

**(74) Agent(s):**

SHENPAT INTELLECTUAL PROPERTY AGENCY; 18C2, 18D, 18E, 18E2 Block B, Lushan Building Chunfeng Road, Nanhu Street, Luohu District Shenzhen, Guangdong 518001 (CN)

**(54) Title (EN):** SEMICONDUCTOR DEVICE, TERMINAL DEVICE, CAMERA, AND LIGHT MODULE

**(54) Title (FR):** DISPOSITIF À SEMI-CONDUCTEUR, DISPOSITIF TERMINAL, CAMÉRA ET MODULE LUMINEUX

**(54) Title (ZH):** 一种半导体器件、终端设备、相机、光模块

**(57) Abstract:**

**(EN):** Disclosed in the present application is a semiconductor device, wherein in the semiconductor device, a barrier layer is disposed between a top transparent electrode, i.e. a second electrode, and a bottom functional layer; the barrier layer may act as a barrier protective layer of the bottom functional layer, and may effectively prevent impact damage to the bottom functional layer during an electrode preparation process, which is beneficial in increasing the yield and reliability of a device. Additionally, further disclosed in the present application are a terminal device comprising the semiconductor device, a camera, and a light module.

**(FR):** La présente invention concerne un dispositif à semi-conducteur, dans lequel, dans le dispositif à semi-conducteur, une couche barrière est disposée entre une électrode transparente supérieure, c'est-à-dire une seconde électrode, et une couche fonctionnelle inférieure; la couche barrière peut agir comme une couche protectrice barrière de la couche fonctionnelle inférieure, et peut empêcher efficacement un endommagement par impact de la couche fonctionnelle inférieure pendant un processus de préparation d'électrode, ce qui est avantageux pour augmenter le rendement et la fiabilité d'un dispositif. De plus, la présente invention concerne en outre un dispositif terminal comprenant le dispositif semi-conducteur, une caméra et un module lumineux.

**(ZH):** 本申请公开了一种半导体器件,在该半导体器件中,在顶透明电极即第二电极以及底部功能层之间设置有阻隔层,该阻隔层可以作为底部功能层的阻隔保护层,能够有效防止顶电极制备过程中对底部功能层的冲击损坏,有利于提升器件良率和可靠性。此外,本申请还公开了一种包含该半导体器件的终端设备、相机和光模块。

**International search report:**

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## **International Report on Patentability (IPRP) Chapter II of the PCT:**

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European Patent Office (EPO) : AL, AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HR, HU, IE, IS, IT, LT, LU, LV, MC, MK, MT, NL, NO, PL, PT, RO, RS, SE, SI, SK, SM, TR

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Eurasian Patent Organization (EAPO) : AM, AZ, BY, KG, KZ, RU, TJ, TM

### **Declarations:**

Declaration made as applicant's entitlement, as at the international filing date, to claim the priority of the earlier application, where the applicant is not the applicant who filed the earlier application or where the applicant's name has changed since the filing of the earlier application (Rules 4.17(iii) and 51bis.1(a)(iii))